

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hattangady et al. Art Unit: TBD
Serial No.: TBD Examiner: TBD
Filing Date: 02/19/2004 Docket No.: TI-31017.1
Customer No.: 23494 Conf. No.: TBD
Title: SEMICONDUCTOR WITH A NITRIDED SILICON GATE OXIDE AND
METHOD

PRELIMINARY AMENDMENT

Commissioner of Patents
P. O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Prior to the review of the above subject patent application, please make the following amendments:

In the Specification:

Please amend the specification by inserting before the first line the sentence:

--This is a divisional application of Serial No. 10/326,188 filed 12/20/2002.
now U.S. Patent 6,716,695

In the Claims:

Please cancel Claims 1-15.

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